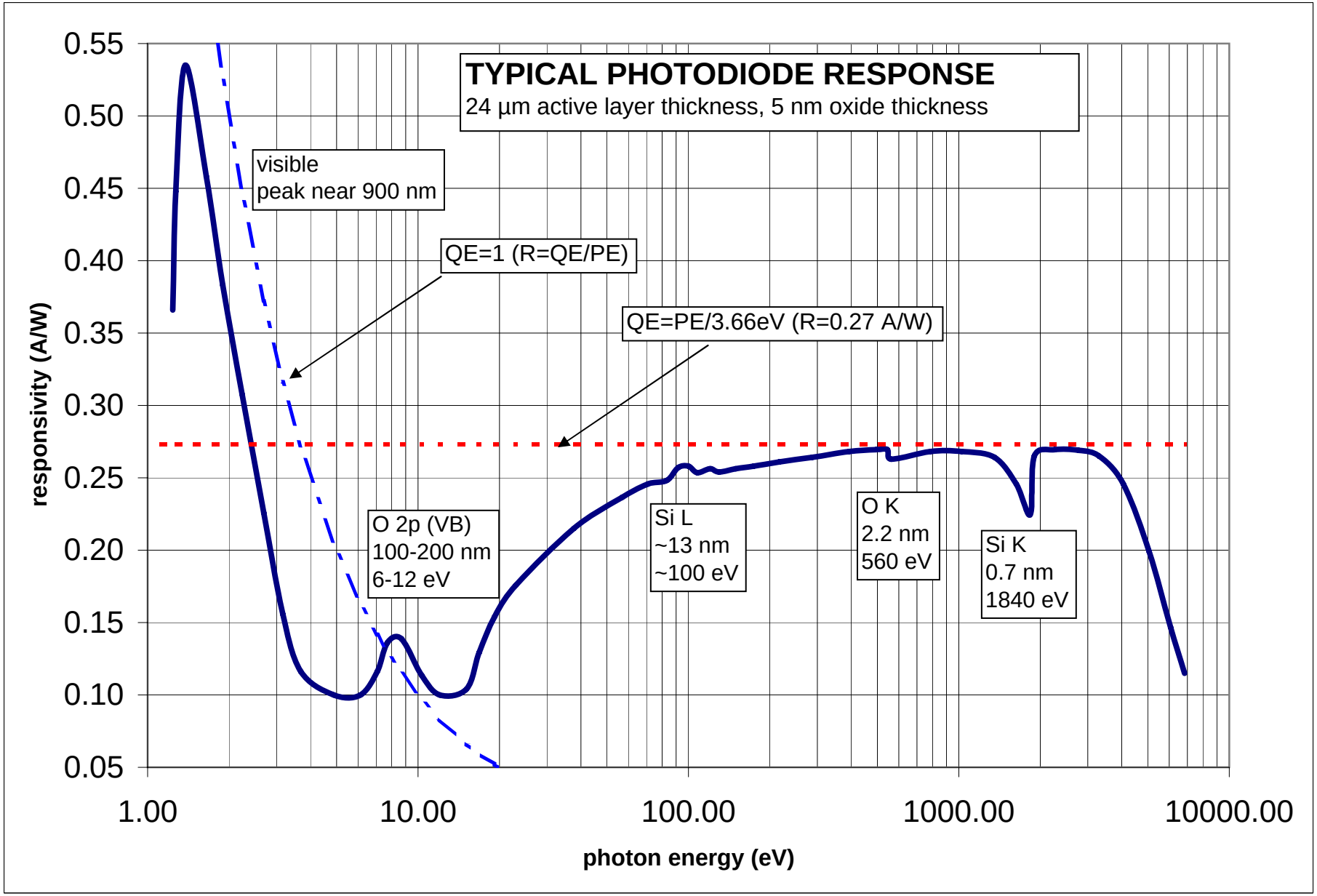
TYPICAL PHOTODIODE RESPONSE
24 µm active layer thickness, 5 nm oxide thickness
visible
peak near 900 nm
QE=1 (R=QE/PE)
QE=PE/3.66eV (R=0.27 A/W)
O 2p (VB)
100-200 nm
6-12 eV
Si L
~13 nm
~100 eV
O K
2.2 nm
560 eV
Si K
0.7 nm
1840 eV
responsivity (A/W)
0.55
0.50
0.45
0.40
0.35
0.30
0.25
0.20
0.15
0.10
0.05
1.00
10.00
100.00
1000.00
10000.00
photon energy (eV)